

Product Summary

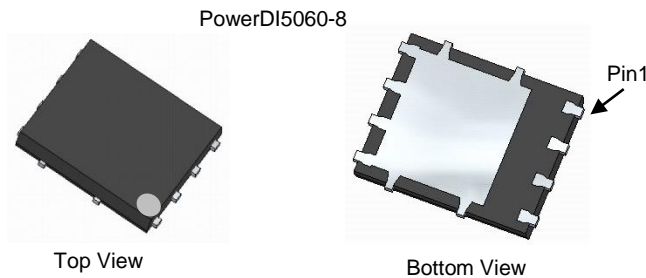
| BV _{DSS} | R _{DS(ON)} Max | I _D T _C = +25°C |
|-------------------|--------------------------------|------------------------------------------|
| 100V | 14.5mΩ @ V _{GS} = 10V | 50.5A |
| | 19.5mΩ @ V _{GS} = 6V | 43.6A |

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)}, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

- Motor Control
- DC-DC Converters
- Power Management

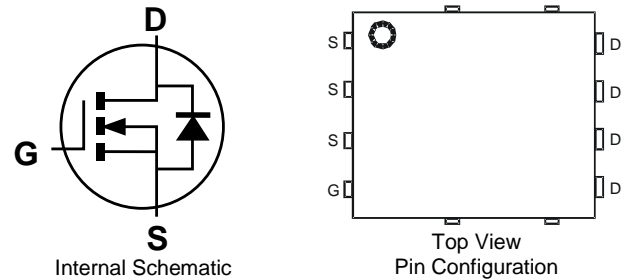


Features

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production—Ensures More Reliable and Robust End Application
- Thermally Efficient Package—Cooler Running Applications
- Low R_{DS(ON)}—Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

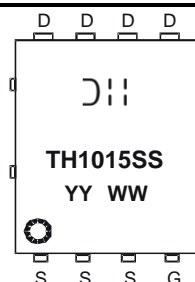


Ordering Information (Note 4)

| Part Number | Case | Packaging |
|------------------|---------------|------------------|
| DMTH10H015SPS-13 | PowerDI5060-8 | 2500/Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, see <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DII = Manufacturer's Marking
 TH1015SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 = 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---------------------------------------------------------|--------------|---------------------------------------------------|------------------|--------------|------|
| Drain-Source Voltage | | | V _{DSS} | 100 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 5) V _{GS} = 10V | Steady State | T _A = +25°C T _A = +100°C | I _D | 8.4 5.9 | A |
| | Steady State | T _C = +25°C T _C = +100°C | I _D | 50.5 35.7 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 120 | A |
| Maximum Continuous Body Diode Forward Current (Note 5) | | | I _S | 1.5 | A |
| Avalanche Current (Note 7) L = 3mH | | | I _{AS} | 7.5 | A |
| Avalanche Energy (Note 7) L = 3mH | | | E _{AS} | 85 | mJ |
| Avalanche Current, L = 0.1mH | | | I _{AS} | 15.8 | A |
| Avalanche Energy, L = 0.1mH | | | E _{AS} | 12.5 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|--------------------------------------------------|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | P _D | 1.5 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | R _{θJA} | 98 | °C/W |
| Total Power Dissipation | T _C = +25°C | P _D | 55 | W |
| Thermal Resistance, Junction to Case | | R _{θJC} | 2.7 | °C/W |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +175 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|-----------------------------------------|---------------------|-----|------|------|------|--------------------------------------------------------------------------------------------|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 100 | — | — | V | V _{GS} = 0V, I _D = 1mA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | 1 | µA | V _{DS} = 80V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 2 | — | 4 | V | V _{DS} = V _{GS} , I _D = 250µA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 11.3 | 14.5 | mΩ | V _{GS} = 10V, I _D = 20A |
| | | — | 14.7 | 19.5 | | V _{GS} = 6V, I _D = 20A |
| Diode Forward Voltage | V _{SD} | — | 0.9 | 1.3 | V | V _{GS} = 0V, I _S = 20A |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C _{iss} | — | 2343 | — | pF | V _{DS} = 50V, V _{GS} = 0V f = 1MHz |
| Output Capacitance | C _{oss} | — | 487 | — | | |
| Reverse Transfer Capacitance | C _{riss} | — | 26 | — | | |
| Gate Resistance | R _G | — | 0.69 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge | Q _G | — | 30.1 | — | nC | V _{DD} = 50V, I _D = 10A, V _{GS} = 10V |
| Gate-Source Charge | Q _{GS} | — | 7.5 | — | | |
| Gate-Drain Charge | Q _{GD} | — | 6.5 | — | | |
| Turn-On Delay Time | t _{D(ON)} | — | 9.8 | — | ns | V _{DD} = 50V, V _{GS} = 10V, I _D = 10A, R _G = 6Ω |
| Turn-On Rise Time | t _R | — | 7.8 | — | | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 22.5 | — | | |
| Turn-Off Fall Time | t _F | — | 9.6 | — | | |
| Reverse Recovery Time | t _{RR} | — | 43.1 | — | ns | I _F = 10A, di/dt = 100A/µs |
| Reverse Recovery Charge | Q _{RR} | — | 65.1 | — | nC | |

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to product testing.

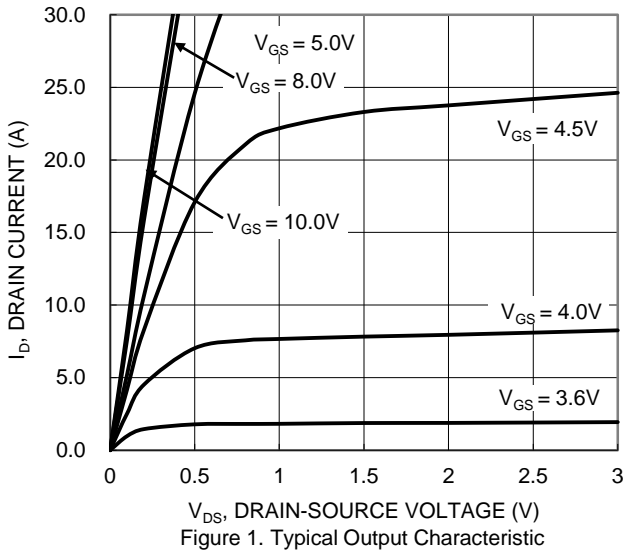


Figure 1. Typical Output Characteristic

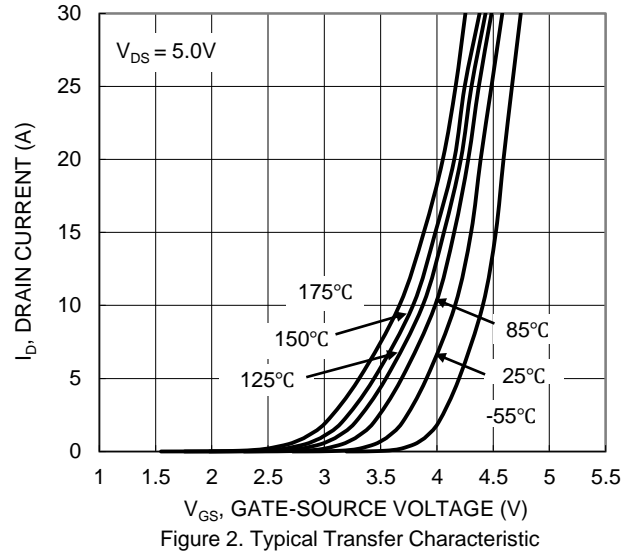


Figure 2. Typical Transfer Characteristic

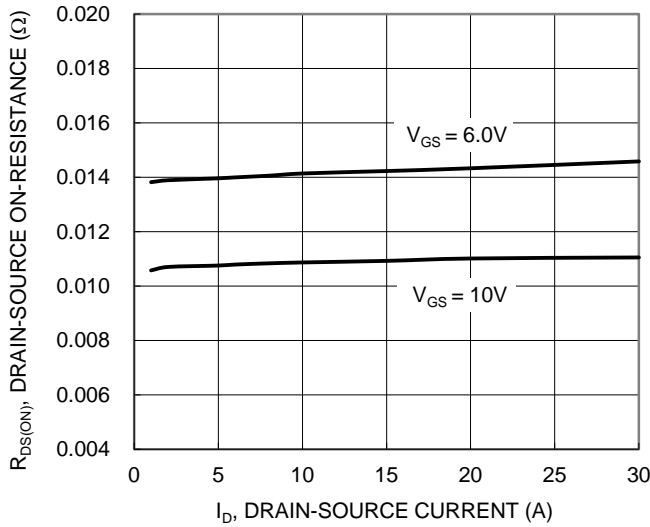


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

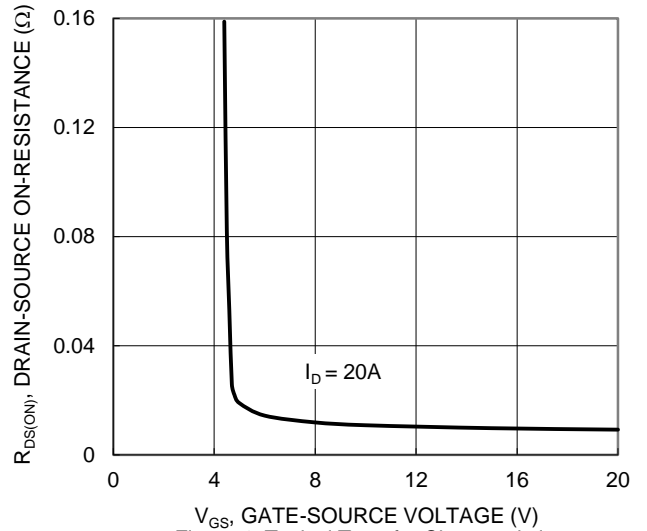


Figure 4. Typical Transfer Characteristic

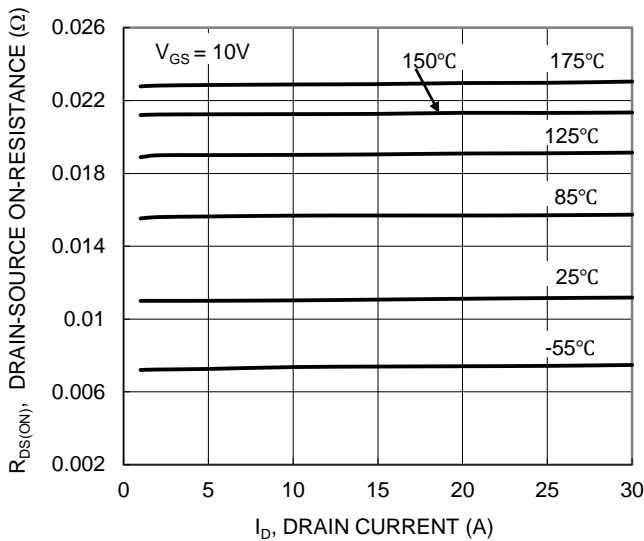


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

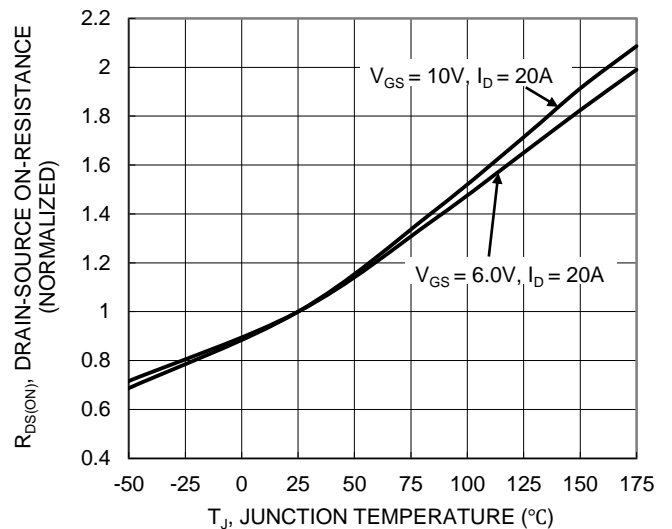
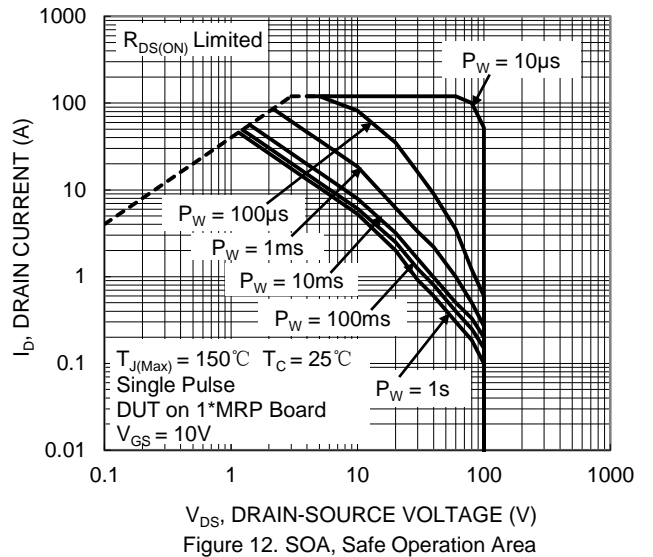
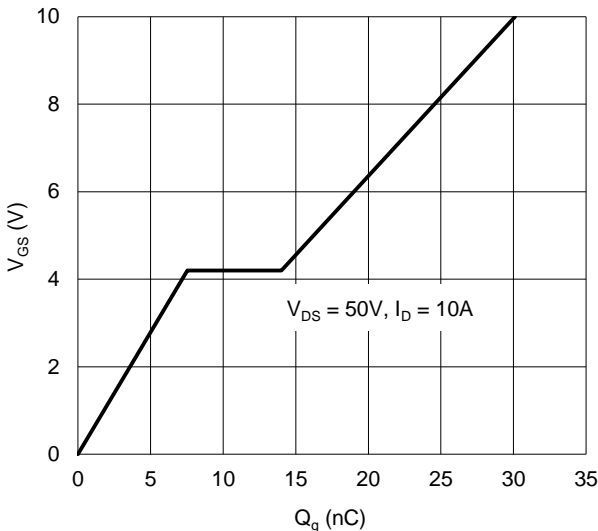
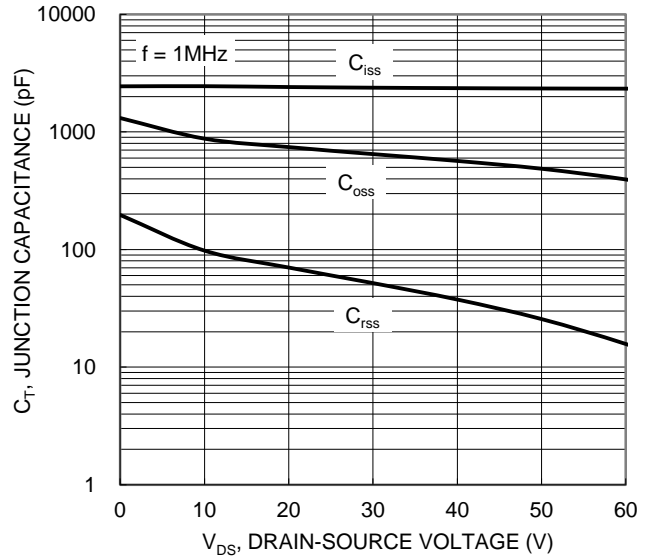
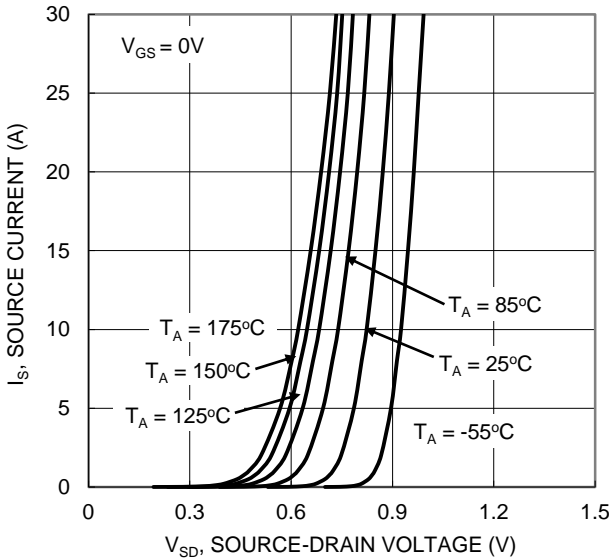
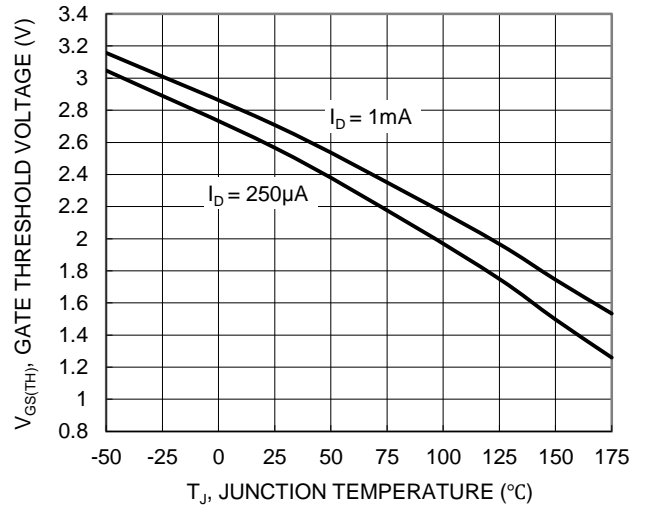
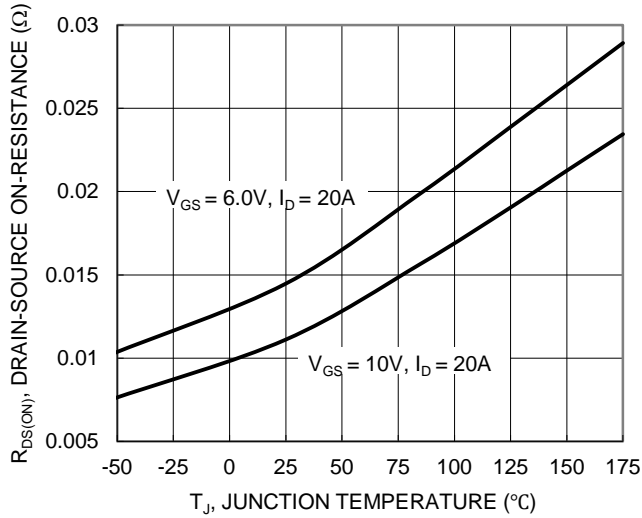


Figure 6. On-Resistance Variation with Temperature



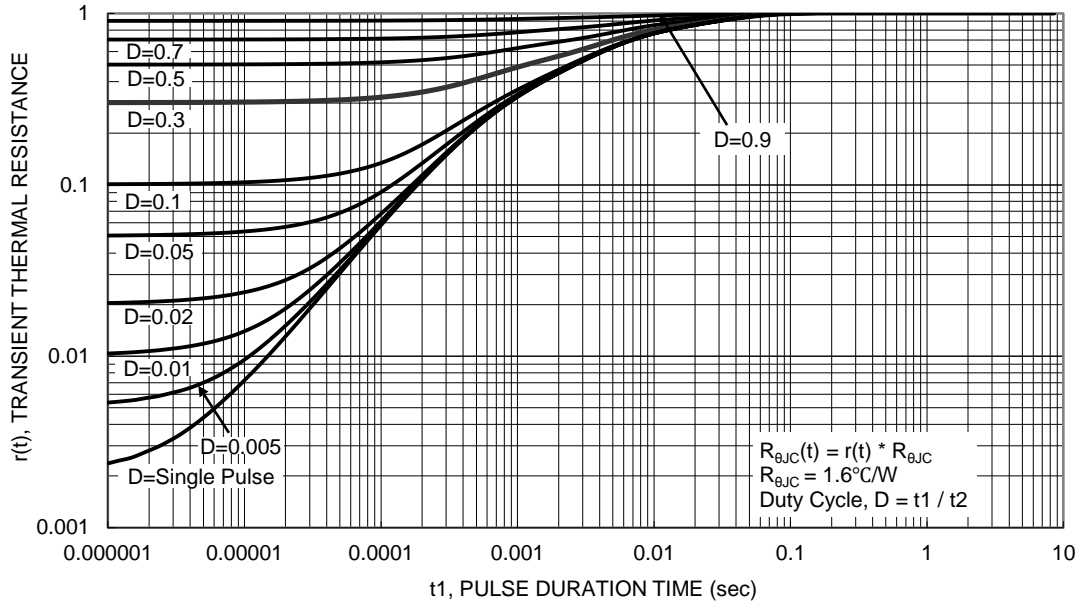
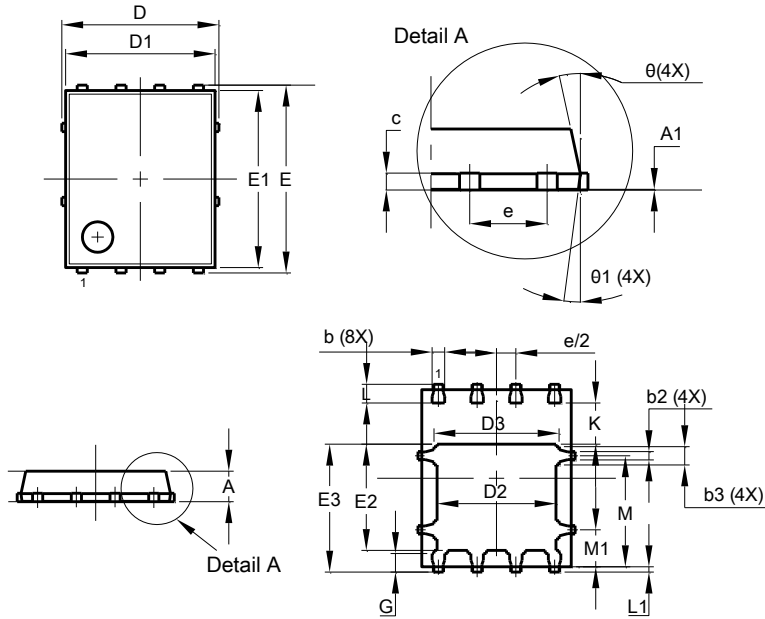


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

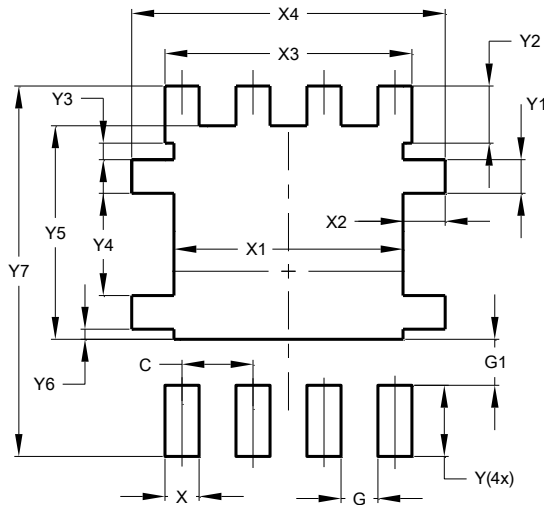


| PowerDI5060-8 | | | |
|----------------------|----------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.10 | 1.00 |
| A1 | 0.00 | 0.05 | - |
| b | 0.33 | 0.51 | 0.41 |
| b2 | 0.200 | 0.350 | 0.273 |
| b3 | 0.40 | 0.80 | 0.60 |
| c | 0.230 | 0.330 | 0.277 |
| D | 5.15 BSC | | |
| D1 | 4.70 | 5.10 | 4.90 |
| D2 | 3.70 | 4.10 | 3.90 |
| D3 | 3.90 | 4.30 | 4.10 |
| E | 6.15 BSC | | |
| E1 | 5.60 | 6.00 | 5.80 |
| E2 | 3.28 | 3.68 | 3.48 |
| E3 | 3.99 | 4.39 | 4.19 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.71 | 0.61 |
| K | 0.51 | - | - |
| L | 0.51 | 0.71 | 0.61 |
| L1 | 0.100 | 0.200 | 0.175 |
| M | 3.235 | 4.035 | 3.635 |
| M1 | 1.00 | 1.40 | 1.21 |
| θ | 10° | 12° | 11° |
| θ1 | 6° | 8° | 7° |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| X3 | 4.420 |
| X4 | 5.610 |
| Y | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y7 | 6.610 |

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